Restoring the Planckian regime via suppression of charge density waves in an underdoped cuprate superconductor

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The normal state of cuprates is dominated by the “strange metal” phase that, near optimal doping, shows a linear temperature dependence of the resistivity persisting down to the lowest $T$, when superconductivity is suppressed. For underdoped cuprates this behavior is lost below the pseudogap temperature $T^\ast$, where Charge Density Wave (CDW) together with other intertwined local orders characterize the ground state. Here we show that the $T$-linear resistivity of highly strained, ultrathin and underdoped YBa$_2$Cu$_3$O$_{7-\delta}$ films is restored when the CDW amplitude, detected by Resonant Inelastic X-ray scattering, is suppressed. This observation points towards an intimate connection between the onset of CDW and the departure from $T$-linear resistivity in underdoped cuprates, a link that was missing until now. It also illustrates the potentiality of strain control to manipulate the ground state of quantum materials.

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High critical Temperature cuprate Superconductors (HTS) belong to a whole class of materials where strong correlations play a fundamental role, and whose unconventional properties might require abandoning traditional concepts of solid state physics for a proper description. The "strange metal" phase of HTS, which exhibits a linear temperature dependence of the resistivity, persisting to the lowest $T$ when superconductivity is suppressed, is undoubtedly one of the most striking manifestations of the strong correlations. A possible way to model this peculiar behavior is in terms of a new fundamental time scale, defined by the Planckian time $\tau = \hbar/k_BT$ (where $\hbar$ and $k_B$ are the reduced Planck and Boltzmann constants), representing a lower bound on the time for a system to reach local equilibrium as $T \to 0$. The Planckian time $\tau$, once substituted in the Drude formula, gives the $T$-linear dependence of the resistivity that has been observed to hold not only for all cuprates at optimal doping but also in other strongly correlated systems, like pnictides and magic angle bilayer graphene. This behavior seems fundamentally different from that observed in more conventional metals, where a $T$-linear dependence of the resistivity is found only at high temperatures where phonon scattering is thought to dominate the transport.

Systems based on local interactions between quasiparticles, like ordinary metals, can never thermalize in such a short timescale at low temperatures; to thermalize on the Planckian time scale every particle must be entangled with every other particle in the system. In strongly entangled systems one needs therefore to abandon the traditional notion of Landau quasiparticles as building blocks of matter. In this respect angle resolved photoemission spectroscopy (ARPES) data have indeed confirmed the absence of quasiparticle excitations at optimal doping.

Going into the overdoped regime, the recovery of an almost $T^2$ dependence of the resistivity, typical of a Fermi liquid, appears natural as a consequence of the increased screening of the electron-electron interactions due to the higher charge carrier density. In underdoped cuprates, instead, it is at first surprising that the breakdown of the Planckian time regime, seen as consequence of the strong correlations, occurs. At this low doping the electron-electron interaction should be stronger than at optimal doping due to the reduced screening following from a smaller carrier density. However, the Planckian dissipation, that seems to be the driving mechanism behind the "strange metal" phase, leading to dense long-range entanglement, can only occur in the quantum critical region of the phase diagram near a putative quantum critical point, where quantum and thermal fluctuations are of equal importance.
Outside the quantum critical region, the recovery of the quasiparticle notion has been shown by spectroscopic measurements (14). In underdoped cuprate superconductors, at temperatures below what is known as the pseudogap temperature \( T^* \), where states are missing at the Fermi energy, a plethora of intertwined electronic local ordering phenomena occurs (1,15,16,17,18,19), where Charge Density Wave (CDW) (17) is the most prominent one. Furthermore, it is below \( T^* \) that the \( T \)-linear resistivity dependence of the “strange metals” breaks down.

To test the idea that local orders can be responsible for the departure of the resistivity from the \( T \)-linear behaviour, one needs a strategy to properly tune the local properties of underdoped HTS. In particular, the CDW can be strongly modified under pressure (20,21), strong magnetic fields (22) and strain in crystals (23) and thin films (24).

Here we use the geometric modification of the YBCO unit cell, under the strong strain induced by the substrate in ultrathin films, to tune the ground state of the material. We show that the \( T \)-linear resistivity dependence is completely recovered (down to the superconducting critical temperature \( T_c \)) along the \( b \)-axis when the CDW, detected by Resonant Inelastic X-ray scattering (RIXS) is suppressed along the \( a \)-axis. The films span a wide range of hole-doping \( p \), going from the strongly underdoped (\( p \approx 0.10 \)) up to the optimally doped (\( p \approx 0.17 \)) regime (25), see Supplemental Material for more details. The strain has been modified both by changing the substrate and by varying the film thickness \( t \) in a range from 50 nm down to 10 nm. We have used (110) oriented MgO and 1° vicinal angle (001) SrTiO\(_3\) (STO) substrates to grow untwinned YBCO films (26). When the YBCO thickness is reduced to a few unit cells (\( t = 10 \) nm), films grown on MgO are characterized by a significant elongation of the \( b \)-axis and contraction of the \( c \)-axis, with the total volume of the unit cell unchanged compared to relaxed systems (see Fig. 1A). For films grown on vicinal cut STO, the YBCO unit cell is instead almost thickness independent (see Fig. S1).

Figure 1B shows a typical device used to measure the resistivity as a function of the temperature. The devices are patterned at an angle \( \phi \) with respect to the YBCO [100] direction by using a carbon mask in combination with electron beam lithography and \( \text{Ar}^+ \) ion milling (25,27) (see Supplemental Material for more details).

Figure 1C shows the temperature dependence of the resistivity \( \rho \), measured in two devices oriented along the YBCO \( a \)- and \( b \)-axis (\( \phi = 0° \) and 90° respectively) realized in an underdoped
50 nm thick film grown on an MgO substrate. The resistivity anisotropy ratio at $T=290$ K, defined by $\rho_a(290 \text{ K})/\rho_b(290 \text{ K})$ is around 1.2, a value fully compatible with the level of hole doping (28). The temperature $T_L$, estimated as the temperature below which the resistivity departs from a linear temperature dependence, is approximately the same for both devices, and it is very close to the temperature $T^*$ associated with the pseudogap onset for YBCO single crystals at comparable levels of doping (29).

Figure 1D shows analogous data for two devices patterned on a 10 nm thick film on MgO (grown with the same deposition conditions as the 50 nm thick film) with comparable doping $p$ as the one in Figure 1C. The superconducting critical temperature $T_c$ remains almost unchanged (30), in line with the fact that the carrier density, extracted by measurements of the Hall coefficient, is almost identical in 10 and 50 nm thick films (see Fig. S2 for more details).

The overall $\rho(T)$ behaviour is instead very different. We observe two striking features, namely 1) the in-plane anisotropy of the resistivity $\rho_a(290 \text{ K})/\rho_b(290 \text{ K})$ is much higher compared to the 50 nm thick film and 2) the resistivity along the $b$-axis $\rho_b(T)$ has a much broader temperature range of linearity. This second aspect is crucial, since it indicates that the “strange metal” behaviour is restored in ultrathin underdoped YBCO. What are the conditions for this to happen?

The most prominent effect we encounter by reducing the thickness is that the YBCO $b$-axis strongly expands, while the $a$-axis is only slightly modified; at the same time the total volume of the cell remains unaltered, as a consequence of a $c$-axis contraction. One of the effects of the strain is therefore to increase the orthorhombicity of few-nm-thick films. For 10 nm thick underdoped films ($p\approx0.12$) the values of the lattice parameters $a$ and $b$ are similar to those of YBCO with a much higher doping (31), close to the optimal doping. This fact can explain the anomalously high anisotropy ratio $\rho_a(290 \text{ K})/\rho_b(290 \text{ K})$ that we observe (see Fig. 1D), a value one would have expected for an optimally doped YBCO crystal (28). The wider $T$-linear behaviour of $\rho_b(T)$ in ultrathin films is not observed in YBCO on vicinal angle STO substrates. Here $T_L$ does not change: it is the same along the $a$-axis and the $b$-axis and going from 50 nm to 10 nm thick films (see Fig. S3).

We have therefore arrived at the main result of our paper: a specific strain in underdoped 10 nm thick YBCO films on MgO substrate leads to a broader range of $T$-linear resistivity along the $b$-axis. To understand the generality of this effect, that is not “accidental” but due to profound
structural-induced modifications of the ground state, we have measured $\rho(T)$ as a function of the doping $p$ (see Fig. 2A, 2B) and of the angle $\phi$ (see Fig. 2C, 2D) for 10 nm thick YBCO films on MgO substrates (as a function of the thickness in Fig. S4).

Figures 2A and 2B show $\rho_a(T)$ and $\rho_b(T)$ for different oxygen doping. The $\rho_a(T)$ curves are rather conventional and in agreement with previous results (25,29). The extracted $T_c$ and $T_L$ are in line with those reported for single crystals for the same level of doping. As $p$ is reduced, $T_L$ increases, and the lower temperature region, where the resistivity exhibits a quadratic dependence on the temperature, expands. For doping levels approaching $p \approx 0.10$, a saturation in $\rho(T)$ develops at temperatures below the quadratic regime (25,29,32). However, $\rho_b(T)$ (see Fig. 2B) looks very different. For $p \approx 0.14$ the $T$-linear dependence extends to the entire temperature range until superconductivity sets in. At this doping we have completely recovered the strange metal behaviour following from dissipation on the Planckian time scale. The situation changes at lower doping: for $p \approx 0.10$, the extracted $T_L$ along $b$ is close to the value along the $a$-axis (see Figs. 2C-2D), while $\rho_b(T)$ shows a pronounced upturn at low temperature before the superconducting transition. The upturn of the $\rho_b(T)$, in our 10 nm thick YBCO films, is observed at higher doping compared to the $a$-axis $\rho_a(T)$ (see Figs. 2A-2B); indeed it appears already at $p = 0.13$. This upturn in the resistivity has been attributed to the loss of high mobility electron pockets because of the CDW order ending at $p \approx 0.08$ (32) and/or to the proximity to the antiferromagnetic Mott insulator through spin density waves (SDW) (32,33,34). Therefore, the doping dependence of $\rho_b(T)$, concerning both the extension of the $T$-linear resistivity regime and its upturn in a range of doping significantly higher than for single crystals, points towards a strong involvement of the CDW order in the phenomenology we observe.

To characterize the CDW order in the YBCO films we have used resonant inelastic x-ray scattering (RIXS) at the Cu $L_3$ edge (~930 eV) (see Supplemental Material). We investigated films with a thickness of 10 and 50 nm grown on both MgO and STO at the doping $p \approx 0.125$ where the intensity of the CDW is strongest (17,35). To isolate the contribution of the CDW we measured RIXS spectra at $T = 70$ K, i.e. close to $T_c$ where the CDW signal is maximized, and at $T = 200$ K, a temperature which is – at any $p$ doping – above the onset of CDW order. The CDW peak has been explored along $a$ and $b$ with two orthogonal cuts along the $H$ and the $K$ directions of reciprocal space, centered around the wave vector of the CDW $q_C^{CDW} = (H_{CDW}, K_{CDW})$. Figures 3A and 3B
show, for a 50 nm thick film on MgO, the quasi-elastic component of the RIXS spectra along the $a$-axis and $b$-axis, as a function of $H$ at $T=70$ K and $T=200$ K. Along both directions, at $T=200$ K only a broad peak is present (see red regions in Figs. 3A and 3B); at $T=70$ K, the signal is given by the sum of a broad peak (similar to that measured at high temperature) and of a narrow peak. This narrow, temperature-dependent, peak is a signature of CDW; the broad, almost temperature-independent, peak is instead a signature of short-ranged charge density fluctuations (CDF) (36), i.e. charge modulations, precursors of CDW, which are present in the phase diagram at any temperature and in a very broad doping range, including the overdoped region. Figures 3C and 3D report the same measurements, as in Figs. 3A and 3B, for a 10 nm thick film on MgO. Here, along the $b$-axis (see Fig. 3D) both the CDW and the CDF peaks are very similar to those measured in the thick film. Along the $a$-axis (see Fig. 3C), the situation is instead dramatically different. The broad-in-$q// CDF$ peak is unchanged with respect to the 50 nm thick sample; on the other hand, the narrow CDW peak, emerging at lower temperature, is almost negligible. This occurrence has been verified on the same sample, measuring along the $K$ direction (see Fig. S5), and on other ultrathin films on MgO with different $p$ doping (see Fig. S6).

Similar measurements on films grown on STO substrates show that for 10 nm thick films the CDW intensity along the $a$- and $b$-axis are comparable with those in thicker films (see Fig. S7). It is worth considering that our films are not perfectly untwinned (the untwinning degree is $\approx85\%$ for films grown on MgO, $\approx90\%$ for films grown on STO). The small temperature dependent CDW signal measured along the $a$-axis in the 10 nm films on MgO can be partially due to twinning domains. Indeed, once the twinning is taken into account, the actual CDW signal becomes effectively negligible in the $a$-axis direction. We conclude that in 10 nm thick films on MgO the CDW is unidirectional and directed along the $b$-axis, while the CDW in YBCO grown on STO is thickness-independent.

This important finding shows for the first time a clear correlation between the $T$-linear dependence of $\rho(T)$ and the charge order: our data show that the recovery of the $T$-linear resistivity along the $b$-axis is associated to the suppression of the CDW along the YBCO $a$-axis. In this scenario, only CDF survive in the system at any temperature, which might be relevant both for Planckian metal (37) and marginal Fermi liquid theories (38) of the strange metal.
Let us elaborate on the possible interpretation of this result in terms of modification of the YBCO unit cell by strain. For YBCO thin films on MgO the orthorhombicity increases and the $c$-axis compresses, while the doping, as shown by Hall measurements on 10 nm and 50 nm thick films, and the superconducting critical temperature, essentially remain unchanged (see Fig. S2). Our measurements therefore point towards a “geometry” dependent nature of the CDW phenomenon and to a strong involvement of the orthorhombicity. This would be in line with theoretical predictions of unidirectional charge density wave order along the $b$-axis in presence of nematicity/orthorhombicity (39,40). We can also exclude that the observed phenomenology can be attributed to structural changes of the CuO chains along the $b$-axis in 10 nm films. For overdoped films, where the conductivity of the chains causes an upward deviation from linearity in $\rho(T)$, we observe the same $\rho_b(T)$ dependence for 50 nm and 10 nm films and very close $T_l$ (see Fig. S2), which excludes CuO chain modification effects in our very thin films.

At the same time the combined transport and RIXS measurements show that the stabilization of a CDW phase in underdoped HTS is a crucial actor for restoring the quasiparticle picture of the excitations, through its possible connection to the pseudogap, responsible for a reduced density of states at the Fermi level. Indeed, missing states at the Fermi energy remove scattering mechanisms which mediate the spreading of long-range entanglement that leads to Planckian dissipation. When this happens, the Planckian time $\tau = \hbar/k_B T$ is not any longer the representative relaxation time of the system, and the resistivity ceases to be linear in temperature.

However, there is still an issue to be addressed: why – in our films – the disappearance of the CDW along the YBCO $a$-axis causes a recovery of the $T$-linear dependence of the resistivity along the $b$-axis (see Figs. 1D and 3C)? It is not uncommon in other compounds that the occurrence of a unidirectional CDW phenomenon affects the transport properties in a direction orthogonal to the CDW $q$-vector (41). In the case of YBCO, a possible reason could be that the disappearance of the CDW along the $a$-axis can correspond to a closing off of the Fermi arcs along the $b$-axis (see Fig. 4A), due to the increased orthorhombicity/nematicity in thin films as suggested in Ref. 40. Since the direction of transport is orthogonal to the Fermi surface, the closure of the pseudogap around the $b$-axis direction would lead to an increased density of low energy states available for transport and scattering along the $b$-axis, thereby making Planckian dissipation possible at lower temperatures. The transport along the $a$-axis instead remains mostly unaffected. This scenario can
also explain the angular dependence of $T_L$ (see Fig. 2D) which sharply changes for $\phi$ close to 90° (corresponding to the \textit{b}-axis), possibly reflecting the change in the Fermi arcs with a closing off along the \textit{b}-axis (see Fig. 4A).

Although not crucial for the main conclusion of the paper, we briefly mention that the above interpretation, in terms of states available for transport, is consistent with the “strange metal” phase of HTS having its origin in a Quantum Critical Point (QCP) at $T=0$. In terms of the QCP phenomenology (42) the increased density of low energy states along the \textit{b}-axis is reflected in a smaller value of the characteristic energy scale $\Delta$, where $\Delta$ can be viewed as the lowest energy for which there is some significant density of states contributing to transport, and therefore connected to the pseudogap. The energy scale $\Delta$ is also related to the characteristic length scale $\xi$ of correlations in the system through $\Delta \sim \xi^z$, where $z$ ($z>0$) is the dynamical critical exponent. A lower value of $\Delta$, meaning that the states available for transport will be thermally excited at a lower temperature, leads to a larger quantum critical “strange metal” region of the phase diagram in the underdoped region, as visualized in Figure 4B. This is a result of the longer correlation length following from a smaller $\Delta$, and the resulting long-range entanglement underlyning the “strange metal” phase. The restoration of “strange metal” transport along the \textit{b}-axis could therefore potentially be explained by this mechanism. Note that due to the highly non-isotropic form of the Fermi surface, induced by the increased orthorhombicity in 10 nm YBCO thin films, one should view the characteristic energy scale as being different for transport along the \textit{a}- and \textit{b}-axis, i.e. having two separate $\Delta_a$ and $\Delta_b$ (see Fig. 4B).

To conclude, we have demonstrated that the interpretation of the “strange metal” picture of the normal state of HTS in terms of the Planckian time, can also be applied to the underdoped state of the cuprates as expected because of the strong electron-electron correlations. The strain in the nm thick films induces an increased orthorhombicity which highlights the fundamental impact that changing the geometry of the unit cell has on HTS phenomenology. This paves the way for a new ‘geometry based’ class of experiments able to tune and therefore clarify the intertwined ordered phases making up the underdoped region of cuprate HTS.

Our findings also show that the theoretical work has to be directed towards finding a new paradigm of transport in which the charge and heat are not carried by quasiparticles, but by a many-body state that connects a large number of particles through long-range quantum entanglement.


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Fig. 1: Angular dependence of the YBCO in-plane resistivity as a function of the thickness of films on MgO under strain. (A) Lattice parameters (a- b- and c-axis, respectively indicated by squares, triangles and circles) of YBCO as functions of the thickness of films with a hole-doping $p \approx 0.12$ grown on MgO. Thick lines are guides to the eye. (B) False colour scanning electron microscope image of a typical device used to measure the resistivity $\rho$, with the current I flowing at an angle $\phi$ with respect to the YBCO [100] direction (a-axis). The inset shows an overview of the patterned samples. (C) $\rho(T)$ of two devices, oriented along the a- and the b-axis directions, patterned on a 50 nm thick underdoped ($p=0.11$) film. At $T = 290$ K, $\rho_a/\rho_b = 1.2$. The dashed lines are the linear fits of the curves for $T > 250$ K. $T_L$ is the temperature where the resistivity normalized to 290 K deviates by 1% from the linear fit. (D) $\rho(T)$ of two devices, oriented along the a- and the b-axis directions, patterned on a 10 nm thick underdoped ($p=0.12$) film. At $T = 290$ K, $\rho_a/\rho_b = 2.1$. 
Fig. 2: Angular dependence of the in-plane resistivity of the 10 nm YBCO on MgO as a function of the oxygen doping. (A) ρ(T) measured along the a-axis direction of 10 nm thick films, with different doping levels, grown on MgO substrates. T_L is extracted as described in Fig. 1. The dashed regions represent the temperature range above T_L where at each p the T-linear resistivity regime occurs. (B) Same as panel (A), but ρ(T) is measured along the b-axis. (C) ρ(T), normalized to its value at T=290 K, for a 10 nm thick film (p=0.120) on MgO is shown as a function of φ, i.e. with respect to the a-axis direction. For each angle, the temperature T_L has been extracted (black spheres and dots). T_L is approximately constant at any φ, except around φ=90°, where it exhibits a sharp suppression. (D) T_L values as a function of φ for 10 nm thick films with different doping levels (p ≈ 0.099, 0.103, 0.108, 0.117, 0.118, 0.120, 0.123, 0.134, 0.140, 0.147).
**Fig. 3:** Thickness dependence of the CDW in YBCO thin films. (A)-(B) Quasi-elastic scans measured at $T = 70$ K and $T = 200$ K on the 50 nm thin film on MgO along the $(H,0)$ direction, i.e. a-axis (A), and the $(H,K_{CDW})$ direction, i.e. b-axis (B). (C)-(D) Same as panels (A)-(B), but on a 10 nm thick sample. The measurements have been performed along the $(H,0)$ direction, i.e. a-axis (C), and the $(H,K_{CDW})$ direction, i.e. b-axis (D). In the latter sample, the CDW intensity along the $a$-axis is almost negligible. If we take into account the small twin domains ($\approx 15\%$) present in our films, we conclude that in few-unit-cell thick films on MgO the CDW is unidirectional along the $b$-axis. The green line in the inset of each figure shows the direction of the scan relative to the CDW peak in reciprocal space.
Fig. 4: Scenario explaining the anisotropy of the resistivity and CDW in strained thin films. (A) Sketch of the possible reconstruction of the Fermi surface induced by the increased orthorhombicity, adapted from Refs (39,40). Notice the closing of the Fermi arcs near (±π, 0). The dashed lines show the Fermi surface above $T_L$ and the filled lines below $T_L$. (B) YBCO phase diagram in the QCP scenario. The antiferromagnetic and superconducting states are present below $T_N$ and $T_c$. $T_L$ serves as a crossover line between quantum-critical ($\Delta<k_B T$) and non-critical ($\Delta>k_B T$) region. Along the $a$-axis $T_L = T_L^a$ (pink squares) is equal to the pseudogap temperature $T^*$, while it is suppressed to lower temperatures along the $b$-axis (blue triangles). The error bar on $T_L^b$ highlights the uncertainty of determining the correct value due to proximity to $T_c$. The lines are guides to the eye. In this scenario $p_c=0.19$ is the QCP.
Materials and Methods

Samples

The YBa$_2$Cu$_3$O$_{7-\delta}$ (YBCO) films have been deposited by pulsed laser ablation on 5 × 5 mm$^2$ (110) oriented MgO and 1° vicinal angle (001) SrTiO$_3$ substrates. To favor the growth of untwinned films, an anisotropic strain is needed, preventing the random exchange of the $a$ and $b$ axis parameters. On STO this is achieved by the formation of terraces on the surface, therefore the substrate vicinality is the critical control parameter (43); on MgO similar role is played by facets, which are induced by a 5-hours-long in-situ annealing at 790 °C, done before the deposition (26). Details on the sample growth have been previously reported (25). In particular, after the deposition, the films have been slowly cooled down at an oxygen pressure varying in a range between 30 μbar and 600 μbar, to span most of the underdoped side of the YBCO phase diagram.

Benchmark of the quality of the films is the phase diagram we can build from transport measurements (25), which is in qualitative and quantitative agreement with that of YBCO single crystals (29). In particular, the doping $p$ for each film cannot be directly determined, since a precise estimate of the oxygen content $n$ and of the degree of oxygen ordering in the chains can be determined, although with several challenges, only in single crystals. Therefore, using a method successfully used for crystals (44), we have indirectly determined $p$ by the knowledge of $T_c$, in combination with the $c$-axis length obtained via XRD: for films with thickness larger than 30 nm, where the $c$-axis length is strain-, therefore thickness-, independent, the result is that the doping $p$, for every value of critical temperature $T_c$, is in good agreement with the doping $p$ measured in single crystals (in this paper, we refer in particular to Refs. 35,44).

Details on the growth and characterization of our few-unit-cell thick films, the 10 nm thick ones, to which we refer as “ultrathin” in the text, have been previously reported (30). These films are characterized by high crystallinity and by properties representative of the YBCO bulk. In particular, for a fixed doping level, the critical temperature $T_c$ is – within few Kelvin – identical to that of thicker, 50 nm films. The small discrepancy, which becomes more significant when decreasing even more the thickness, is due to the increased broadening of the superconducting transition, explained in terms of the Kosterlitz-Thouless transition in systems which tend to become 2D (30,45).

Determination of the thin film lattice parameters

The lattice parameters of the films have been determined by XRD analysis using a Panalytical X’pert PRO Materials Research 4-axis diffractometer with 4-bounce Ge220 monochromator and PIXcel detector. The $c$-axis parameter has been determined by symmetric 2θ-ω scans, from the angular position of the (00$n$) YBCO peaks. To find out the length of the $a$ and $b$ axis parameters, as well as the twinning state of the films, we have measured the asymmetrical (038)-(308) reflections of YBCO via 2θ-ω maps (see Fig. S1). For films grown on MgO the untwinning degree is in the range 82-85%, while it exceeds 90% for films grown on vicinal angle STO substrates.

Transport measurements

Transport measurements have been carried out using a Quantum Design PPMS, with a 4-point measurement scheme. The devices, through which the current flows, are wires, whose width is in
the range between 5 μm and 15 μm (see Fig. 1B). The voltage probes, orthogonal to the wires, are 10 μm distant. The nanopatterning procedure we have used is based on an amorphus carbon mask, in combination with electron beam lithography and a gentle ion milling. We have routinely used this procedure in recent years to achieve structures that present properties representative of YBCO and unaffected by the nanopatterning procedure, down to 50 nm (27,46,47).

The resistivity of the wires has been measured in the temperature range between 10 K and 290 K. For each measured curve, we have determined the critical temperature \( T_c \) at 90% of the normal resistivity just above the transition. \( T_L \) is instead defined as the temperature where the resistivity, normalized to 290 K, deviates by 1% from a linear fit at high temperatures.

**RIXS measurements**

The RIXS measurements have been taken at the beamline ID32 of the European Synchrotron Radiation Facility (ESRF) in Grenoble using the high-resolution ERIXS spectrometer (48). The YBCO films, which do not require any particular surface preparation prior to the measurements, were mounted on a 6-axis in-vacuum Huber diffractometer. The energy of the incident X-ray beam has been tuned to the maximum of the Cu \( L_3 \) absorption peak, around 931 eV. The instrumental energy resolution was set at 55 meV, determined as the full width at half maximum of the non-resonant elastic scattering from silver paint. Details of the experimental geometry has been already shown in previous papers (49,50): X-rays are incident on the sample surface, which is normal to the YBCO \( c \)-axis, and are scattered by an angle \( 2\theta \). The momentum transfers are given in units of the reciprocal lattice vectors \( a^* = 2\pi/a \), \( b^* = 2\pi/b \), \( c^* = 2\pi/c \). We have worked at \( 2\theta = 149.5^\circ \) in order to get \( \vert q \vert = 0.91 \text{ Å}^{-1} \), which allowed us to cover the whole first Brillouin zone along the [100] and [010] directions (0.5 r.l.u. ≈ 0.81 Å\(^{-1}\)). By rotating the samples around the \( \theta \) and \( \chi \) axes, without moving \( 2\theta \) (in the hypothesis – supported by previous experiment on cuprates - of a small interlayer coupling, therefore of a weak dependence of the charge order on \( L \)), we have changed the in-plane wave vector component \( q_// \), measuring respectively the \( H \) scans and the \( K \) scans. At each \( q_// \) value, the RIXS spectrum has been measured in 2.5 minutes (sum of individual spectra of 15 seconds) for the 50 nm thick films and 7 minutes (sum of individual spectra of 60 seconds) for the 10 nm thick films. The zero-energy-loss line has been determined by measuring a RIXS spectrum, dominated by the elastic contribution, on a 50 nm Au frame sputtered on the edges of the films. The quasi-elastic intensity has been determined by the integral in a range \( ±100 \text{ meV} \) around the zero-energy-loss line. The RIXS spectra presented in Fig. 3 have been normalized to the integral of the inter-orbital \( dd \) excitations, in the range \([-3 \text{ eV}, -1 \text{ eV}] \). We have thoroughly explored four YBCO films: two on MgO (with thickness \( t = 10, 50 \text{ nm} \)) and two on STO (with thickness \( t = 10, 50 \text{ nm} \)). All the films are characterized by a doping level \( p \approx 0.125 \) and \( T_c \) varying in the range between 65 and 70 K. For each film, we have explored the CDW peak along both the [100] and the [010] directions: in the former case, the \( K \) scan (as in Figs. S5A, S5B, S7C and S7G) is performed at a value of \( H \) coinciding with the position of the maximum of the narrow CDW peak, \( H_{\text{CDW}} \); in the latter case, the \( H \) scan (as in Figs. 3B, 3D, S7B and S7F) is performed at a value of \( K \) coinciding with the position of the maximum of the narrow CDW peak, \( K_{\text{CDW}} \). For each investigated film, the intensity and the correlation length of the CDW differ between the two in-plane crystal axis directions (see Fig. 3), as expected in untwinned YBCO (35,51). The almost \( T \)-independent CDF contribution, we have used to single out the CDW, has shown up to be, after the first discovery in YBCO (36), a rather general characteristic of HTS cuprates (52,53,54).
Fig. S1.
X-ray diffraction measurements and determination of the lattice parameters of the untwinned YBCO thin films with \( p = 0.125 \). (A) Symmetric 2\( \theta \)-\( \omega \) scans of the YBCO (006) Bragg peak for films with different thickness grown on MgO. From 2\( \theta_n \), maximum of the (00\( n \)) Bragg peak, the \( c \)-axis lattice parameter can be determined as \( c = \lambda n / 2 \sin(\theta_n) \), where \( \lambda = 1.540598 \) Å is the wavelength of the incident x-ray wave and \( n \) is the peak order. The \( c \)-axis presented in Fig. 1A of the main text is the average of \( n=5 \) and \( n=6 \); its shrinking, as the film thickness is reduced, is associated to the peak maximum, moving to higher 2\( \theta \) value. This is highlighted by the dashed lines. (B)-(G), Asymmetric 2\( \theta \)-\( \omega \) maps of the YBCO (308) and (038) Bragg peaks for films with different thickness grown on MgO. The \( a \)- and \( b \)-axis lattice parameters are determined from the 2\( \theta \) angle corresponding to the maximum respectively of the (308) and of the (038) peak (26). A reduction of the \( c \)-axis should in principle bring to an elongation of both the \( a \)- and \( b \)-axis lattice parameters, if the (308)/(038) peak positions are unchanged. However, as the film thickness is reduced, the (308) peak shifts, as the (00\( n \)) peaks, to higher 2\( \theta \) value, resulting in an \( a \)-axis parameter, whose length is independent of the film thickness. The (038) peak presents instead an opposite shift, moving to lower 2\( \theta \) value: the \( b \)-axis significantly elongates, as shown in Fig. 1A. (H) Table with the values in Å of the lattice parameters of YBCO films grown on MgO and STO, determined from the XRD measurements.
Fig. S2.
Influence of the CuO chains in the transport properties of thin and thick YBCO films. (A) $\rho(T)$ measured along the $b$-axis in $t=10$ nm and 50 nm slightly overdoped films. In the overdoped regime, along the $a$-axis, the high temperature linear resistivity is broken by an upturn, corresponding to the coherence temperature $T_{\text{coh}}$ and to a restoration of the Fermi-Liquid like behavior. Along the $b$-axis, however, at this level of doping the chains contribution to the transport, adding at any temperature a quadratic term to the resistivity, become significant (28). As a consequence of that, the departure from the linear-in-$T$ resistance occurs at a temperature value, $T_{\text{ch}} > T_{\text{coh}}$, which is strongly related to the CuO chains. A variation of the chains in the system, i.e. as a function of the film thickness, is expected to cause a strong variation of $T_{\text{ch}}$. In our panel, the dashed lines are the linear fits for $T>250$ K and $T_{\text{ch}}$ is the temperature where the resistivity, normalized to 290 K, deviates by 1% from the linear fit. Since $T_{\text{ch}}$ is the same in the thin and thick case, we can conclude that the CuO chains are not different in the thin and thick films and thus cannot be at the origin of the increase of in-plane anisotropy observed in the $\rho(T)$ of ultrathin underdoped films. (B) Measurement of the Hall coefficient $R_H$ in patterned Hall bars on $t=10$ nm and 50 nm underdoped ($p = 0.11$) films. Since the shape and magnitude of $R_H(T)$ is qualitatively the same in the thin and thick case, we can be confident that the doping $p$ extracted from the $T_c$ is correct and also that the carrier density is not changed when the thickness of the film is reduced. To get the correct $R_H(T)$ in an orthorhombic system, the measured values has been multiplied by the resistivity anisotropy $R_H(T) = R_H^{\text{meas}}(T) \cdot \rho_a(T)/\rho_b(T)$, as described in Ref. (55).
Fig. S3.
Angular dependence of the YBCO in-plane resistivity as a function of the thickness in films on STO. (A) $\rho(T)$ of two devices, oriented along the $a$- and the $b$-axis directions, patterned on a 50 nm thick underdoped ($p=0.11$) film on STO substrate. At $T=290$ K, $\rho_a/\rho_b = 1.2$. The dashed lines are the linear fits of the curves for $T>250$ K. $T_L$ is the temperature where the resistivity normalized to 290 K deviates by 1% from the linear fit, and it is the same along both directions. (B) $\rho(T)$ of two devices, oriented along the $a$- and the $b$-axis directions, patterned on a 10 nm thick underdoped ($p=0.115$) film on STO. At $T=290$ K, $\rho_a/\rho_b = 1.6$: as observed in Figure S1H, indeed, the orthorhombicity of the YBCO unit cell increases in the ultrathin films, even though less than on the MgO substrates. Moreover, differently than in ultrathin films grown on MgO substrates, here the range of linear-in-$T$ resistivity is unchanged in both directions, i.e. the extracted $T_L$ is the same.
Fig. S4.

Angular dependence of $T_L$ in YBCO films on MgO substrates as a function of the thickness.

(A) The $T_L$, extracted as described in Figure 1, is presented as a function of $\phi$ for four films ($p \approx 0.11 - 0.12$) with thickness $t$ ranging from 10 to 50 nm. As the thickness is reduced, the value of $T_L$ measured along the $b$-axis ($\phi = 90^\circ$) gradually decreases. This implies that the linearity of $\rho$ mainly extends to the whole normal state of YBCO, when the thickness is reduced. Moreover, we observe that $T_L$ is approximately constant from $\phi = 0^\circ$ up to about $\phi = 45^\circ$, followed by a sharp suppression with a minimum at $\phi = 90^\circ$. From this occurrence we infer that the scattering mechanism – if any - responsible of the extension of the linear regime to lower $T$ must be strongly directional. In this figure, the doping level of the $t=10$ nm film is slightly higher, resulting in a lower value of $T_L$ at $\phi = 0^\circ$. The dashed lines are guides to the eye.

(B) $\rho(T)$ measured along the $a$- and the $b$-axis directions of a 10 nm thick underdoped ($p=0.12$) film. With respect to the $\rho(T)$ presented in Figure 1E, here the film has not been patterned into microwires, therefore the current paths are not well defined and a proper angular dependence of the resistivity cannot be measured. However, both the striking features we have observed in the $\rho(T)$ of our ultrathin films on MgO, i.e. the enhanced in-plane anisotropy ratio of the resistivity $\rho_a/\rho_b$ at 290 K and the much broader temperature range of linearity along the $b$-axis, are present. This occurrence confirms that the results we can infer from the $\rho(T)$ are robust and do not depend on possible damages induced into the ultrathin film by the nanopatterning procedure.
**Fig. S5.**

**Thickness dependence of the CDW in YBCO thin films, K scans.** The same scans presented in Figure 3 along the $H$ direction of the reciprocal space are here shown along the $K$ direction. (A), (C) Quasi-elastic scans measured at $T = 70$ K and $T = 200$ K on the 50 nm thin film on MgO along the $(H_{CDW},K)$ direction, i.e. $a$-axis (A), and the $(0,K)$ direction, i.e. $b$-axis (C). (B),(D) Same as panels (A) and (C), but on a 10 nm thick sample. In the latter sample, the CDW intensity along the $a$-axis is almost negligible, similarly to what observed along the $H$ direction. The CDW peaks are split in the reciprocal space: this is a consequence of the buckling of the atomic planes along the $b$-direction, occurring in YBCO films as a consequence of the large lattice mismatch with the MgO substrates (26). On each film, we notice that the maximum intensity of the CDW peak along the $a$-axis is the same when measured along the $H$ and the $K$ direction (when split, $H_{CDW}$ and $K_{CDW}$ are chosen to be in the middle between the two maxima). Same applies for the $b$-axis. This occurrence confirms that the drop of intensity we have observed along the $a$-axis in ultrathin films on MgO cannot be due to a misalignment, but it is an intrinsic effect of the investigated samples.
Fig. S6.

**Doping evolution of the CDW vs thickness in YBCO films on MgO.** RIXS spectra have been measured on two underdoped YBCO films, with thickness of 50 nm and 8.5 nm, grown on MgO substrates. With respect to those presented in Figure 3 and Fig. S5, these films are characterized by a higher oxygen doping of $p \approx 0.13$ ($T_c \approx 75$ K). (A) Quasi-elastic scans measured at $T = 20$ K on the 50 nm thin film on MgO both along the $(H,0)$ direction, i.e. $a$-axis (circles) and along the $(0,K)$ direction, i.e. $b$-axis (triangles). Here the splitting of the CDW peaks along the $(0,K)$ direction is related to the unidirectional buckling of the CuO$_2$ planes along the $b$-axis, previously discussed. (B) Same as panel (A), but on a 8.5 nm thick sample. In the latter sample, the ratio $\text{CDW}(H,0)/\text{CDW}(0,K)$ is lower than in the thicker film as a consequence of the reduction of the charge order along the $a$-axis. This is in agreement to what already observed on the $p \approx 0.125$ sample in the main text. With respect to that sample, here the reduction is not as strong.
CDW as a function of thickness in YBCO on STO and comparison with films grown on MgO.

(A),(B),(C),(D) Quasi-elastic scans measured at $T = 70\text{ K}$ and $T = 175\text{ K}$ on the 50 nm thin film ($p \approx 0.125$) on STO along the $a$-axis [(H,0) and (H$_{\text{CDW}},K$) directions, (A)-(C)] and $b$-axis [(H, K$_{\text{CDW}}$) (0,K) directions, (B)-(D)]. Each scan is shown after subtracting the background, given by the quasi-elastic scan measured along the diagonal [(H,H) direction].

(E),(F),(G),(H) Same as the first four panels, but on a 10 nm thick film ($p \approx 0.125$) on STO substrates. In the latter sample, differently from the film grown on MgO, the CDW intensities along the $a$-axis and $b$-axis are comparable.

(I),(J) The CDW area, determined as the difference between the low temperature and the high temperature quasi-elastic scans measured along the $H$ (triangles) and $K$ (crosses) directions, and normalized to the $b$-axis contribution, is plotted as a function of the thickness for films both grown on MgO (I) and STO (J). The values have been obtained after removing for each direction the signal coming from the twin domains ($\approx 15\%$ for films grown on MgO, $\approx 10\%$ for films grown on STO). The RIXS measurements tells that on MgO substrates, the CDW signal along YBCO $a$-axis is suppressed in the 10 nm thick films. Here the CDW is unidirectional along the $b$-axis, as it happens in strongly underdoped ($p \approx 0.08$) YBCO. On STO substrates, on the contrary, the CDW signal along the YBCO $a$-axis is approximately equal to that along the $b$-axis, both on the 10 nm and 50 nm thick films, as expected for YBCO at that level of doping.